



RMo3A-1

A Sub-THz CMOS Molecular Clock with 20 ppt Stability at 10,000 s Based on Dual-Loop Spectroscopic Detection and Digital Frequency Error Integration

M. Kim¹, C. Wang¹, L. Yi², H.-S. Lee¹, and R. Han¹

¹Massachusetts Institute of Technology, Cambridge, USA ²Jet Propulsion Laboratory, California Institute of Technology, USA







Outline



- Motivation and Background
- Prior Arts
- Proposed Chip-Scale Molecular Clock
- Measurement Results
- Conclusions







Motivation

 Highly-stable frequency reference (i.e. clock) is one of the key technologies for a wide range of applications



• Chip-scale molecular clocks provide high stability at low cost by using rotational spectrum of molecules in sub-THz range.

| | Stability | Cost | Power |
|---|-------------------------------------|----------|--------|
| Crystal/MEMS Oscillators | 10 ⁻⁴ - 10 ⁻⁸ | < \$1 | ~ 1mW |
| Oven-Controlled Crystal/MEMS Osillators | ~ 10 ⁻¹⁰ | ~ \$100 | ~1W |
| Chip-Scale Atomic Clocks (CSACs) | ~ 10-11 | > \$1000 | ~100mW |
| Chip-Scale Atomic Clocks (CSMCs) | ~ 10-11 | ~ \$10 | ~100mW |

3





Sub-THz Molecular Clock



4

- Narrow transition line of carbonyl sulfide (OCS) at $f_0 = 231.061$ GHz
- High stability against environmental variations
- f_{CLK} inherits the stability of OCS absorption line since f_c is locked to f_0





Spectral Curves and Frequency Locking

Nth-Order Harmonic Spectral Curves



5







Prior Chip-Scale Molecular Clock (CSMC)

• 3rd-order detection was used for locking

SOLID-STATE

• $\sigma_v = 3.2 \times 10^{-10}$ @ T = 1s, $\sigma_v = 4.3 \times 10^{-11}$ @ T = 10^3 s







- Long-term stability is limited by the finite loop gain
- Large amplifier gain (K_{amp}) is required to suppress the effect of V_{offset} variations, but K_{amp} is limited due to high even-harmonic components
- Lower SNR in high-order detection due to smaller K_r



Problems in Prior CSMCs

 Theoretical stability limit of highorder locking is higher than fundamental locking

RFI

- Molecular regulation is not provided for τ < 20 s
- Long-term variation and temperature sensitivity of VCXO affects the clock's long-term stability (XO Pulling)



Averaging Time, au





Proposed Chip-Scale Molecular Clock

Proposed Architecture

RMo3A-1



- High SNR from fundamental-mode probing (in the main loop)
- Low long-term drift from high-order probing (in the auxiliary loop)

9





Proposed Architecture





SOLID-STATE

MTT-S IEEE MICROWAVE THEORY &

 $\lambda \gamma \lambda$



Transmitter (TX) Architecture



- Two PLLs are cascaded
- 36-bit DSMs are used

RFIC

• Sine modulation with modulation frequency of f_m is applied in PLL2



Transmitter (TX) Architecture



- Simulated THz power of the quadrupler output = -4.4dBm
- Simulated loss of the SAC = 5.2 dB

RFIC

RFIC

Transmitter (TX) Architecture



- Sine modulator generates $40f_m$, $3f_m$, and f_m clocks and 8-bit sine wave
- *f*_m = 111 kHz



RFIC

Receiver (RX) Architecture



- Fundamental detection's output controls the VCXO (main loop)
- 3rd harmonic signal is followed by a comparator and a digital integrator and its output controls the frequency control word of the PLL1. (auxiliary loop)

14





Receiver (RX) Architecture







Receiver (RX) Architecture



- Even harmonic components have large amplitude and can limit K_{amp}
- Notch filters are used to reject the signal at $2f_m$, $4f_m$, ...





Receiver (RX) Architecture



- Even harmonic components have large amplitude and can limit K_{amp}
- Notch filters are used to reject the signal at $2f_m$, $4f_m$, ...
- 20-phase non-overlapping clock signals generated by a pulse generator drive the switches in notch filters



Chip Micrograph and Packaging





SOLID-STATE



RFIC

Measurement Results: TX/RX Performance



19





*PN*_{RF} @ 2*f*_m : -65 dBc/Hz, *PN*_{CKOUT} @ 1 MHz :-129 dBc/Hz



Measurement Results: Spectral Curves



 $K_r = 8.26 \times 10^{-8}$ V/Hz for fundamental probing • $K_r = 4.51 \times 10^{-8}$ V/Hz for 3rd-order probing

21





22





• Average temperature coefficient: 5.8×10⁻¹⁰ °C⁻¹ without temperature compensation





Performance Summary

[1] C. Wang, JSSC, 2019 [2] C. Wang, JSCC, 2021 [3] D. Ruffieux, ISSCC, 2011 [4] H. Zhang, ISSCC, 2019 [5] Microsemi, SA.45s, 2019

RMo3A-1

| | | [3] | [4] | [5] | [1] | [2] | This Work | |
|------------------------------|-----------------------------|---|---|---|-------------------------------------|---------------------------------------|---|--|
| Implementation | | 0.18 µm CMOS + Vapor Cell w/ Integrated Photonics | Discrete Electronics + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS Chip + Sub-THz Waveguide | | | |
| Frequency | | Ground-Sta | Ground-State Hyperfine Transition of Atoms | | | Rotational Transition of Molecules | | |
| Reference | | ⁸⁷ Rb | 133 (| Ś | 16012C32S | | | |
| Probing Freq. | | 3.417 GHz | 4.596 | GHz | 231.061 GHz | | | |
| Order of Locking | | N/A | | | 1 st | 3 rd | 1 st + 3 rd | |
| ADEV (10 ⁻¹⁰) | <i>т</i> =1s | 4 | 0.67 | 3 | 24 | 3.2(Unlocked) | 5.4 | |
| | <i>т</i> =10s | 1.2 | 0.6 | 1 | 8.6 | 5.4 | 2.4 | |
| | <i>т</i> =10 ⁴ s | 2(@ 7= 400s) | 0.05 | N/A | N/A | 0.88 | 0.2 | |
| Avg. Temp. Coeff.† | | N/A | 0.07×10 ¹⁰ /°C | 0.13×10 ¹⁰ /°C | N/A | 28×10 ¹⁰ /°C ⁺⁺ | 5.8×10 ⁻¹⁰ /°C ⁺⁺ | |
| DC Power | | 26 [‡] | 60 | 120 | 66 | 70 | 71 | |

[†]Defined as (Temperature-induced frequency drift)/(Temperature range), ^{††}w/o temp. compensation, [‡]The power of the physics package and signal processing is not included.





Performance Summary

[1] C. Wang, JSSC, 2019 [2] C. Wang, JSCC, 2021 [3] D. Ruffieux, JSSCC, 2011 [4] H. Zhang, JSSCC, 2019 [5] Microsemi, SA.45s, 2019

RMo3A-1

| | | [3] | [4] | [5] | [1] | [2] | This Work | |
|------------------------------|-----------------------------|---|---|---|---|---------------------------------------|--|--|
| Implementation | | 0.18 µm CMOS + Vapor Cell w/ Integrated Photonics | Discrete Electronics + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS Chip + Sub-THz Waveguide | | | |
| Frequency | | Ground-Sta | Ground-State Hyperfine Transition of Atoms | | | Rotational Transition of Molecules | | |
| Reference | | ⁸⁷ Rb | 133 (| Ś | ¹⁶ O ¹² C ³² S | | | |
| Probing Freq. | | 3.417 GHz | 4.596 | GHz | 231.061 GHz | | | |
| Order of Locking | | N/A | | | 1 st | 3 rd | 1 st + 3 rd | |
| ADEV (10 ⁻¹⁰) | <i>т</i> =1s | 4 | 0.67 | 3 | 24 | 3.2(Unlocked) | 5.4 | |
| | <i>т</i> =10s | 1.2 | 0.6 | 1 | 8.6 | 5.4 | 2.4 | |
| | <i>т</i> =10 ⁴ s | 2(@ 7= 400s) | 0.05 | N/A | N/A | 0.88 | 0.2 | |
| Avg. Temp. Coeff.† | | N/A | 0.07×10 ⁻¹⁰ /°C | 0.13×10 ¹⁰ /°C | N/A | 28×10 ¹⁰ /°C ⁺⁺ | 5.8×10 ¹⁰ /°C ^{††} | |
| DC Power | | 26 [‡] | 60 | 120 | 66 | 70 | 71 | |

[†]Defined as (Temperature-induced frequency drift)/(Temperature range), ^{††}w/o temp. compensation, [‡]The power of the physics package and signal processing is not included.

25





Performance Summary

[1] C. Wang, JSSC, 2019 [2] C. Wang, JSCC, 2021 [3] D. Ruffieux, JSSCC, 2011 [4] H. Zhang, JSSCC, 2019 [5] Microsemi, SA.45s, 2019

RMo3A-1

| | | [3] | [4] | [5] | [1] | [2] | This Work | |
|------------------------------|-----------------------------|---|---|---|---|--|---|--|
| Implementation | | 0.18 µm CMOS + Vapor Cell w/ Integrated Photonics | Discrete Electronics + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS + Vapor Cell w/ Integrated Photonics and Heater + Magnetic Shield | 65 nm CMOS Chip + Sub-THz Waveguide | | | |
| Frequency | | Ground-State Hyperfine Transition of Atoms | | | Rotational Transition of Molecules | | | |
| Reference | | ⁸⁷ Rb | 1330 | Ś | ¹⁶ O ¹² C ³² S | | | |
| Probing Freq. | | 3.417 GHz | 4.596 | GHz | 231.061 GHz | | | |
| Order of Locking | | N/A | | | 1 st | 3 rd | 1 st + 3 rd | |
| ADEV (10 ⁻¹⁰) | <i>т</i> =1s | 4 | 0.67 | 3 | 24 | 3.2(Unlocked) | 5.4 | |
| | <i>т</i> =10s | 1.2 | 0.6 | 1 | 8.6 | 5.4 | 2.4 | |
| | <i>т</i> =10 ⁴ s | 2(@ 7= 400s) | 0.05 | N/A | N/A | 0.88 | 0.2 | |
| Avg. Temp. Coeff.† | | N/A | 0.07×10 ¹⁰ /°C | 0.13×10 ⁻¹⁰ /°C | N/A | 28×10 ⁻¹⁰ /°C ⁺⁺ | 5.8×10 ⁻¹⁰ /°C ⁺⁺ | |
| DC Power | | 26 [‡] | 60 | 120 | 66 | 70 | 71 | |

[†]Defined as (Temperature-induced frequency drift)/(Temperature range), ^{††}w/o temp. compensation, [‡]The power of the physics package and signal processing is not included.





Conclusions

- CSMC can provide high stability at low cost
- Dual-loop CSMC improves Allan Deviation by combining high SNR of fundamental transition probing and environmental robustness of high-order transition probing.
- Digital integration in the frequency-locked loop provides high gain.
- Without temperature compensation, Allan Deviation of $\sigma_y = 2 \times 10^{-10}$

¹¹ @ τ = 10⁴ s was achieved.





Acknowledgement

- This work is supported by JPL and NSF.
 - The authors acknowledge Dr. Stephen Coy, Prof. Keith Nelson, and Prof. Robert Field of MIT for technical discussions and assistance.









Thank You







